IN THE CLAIMS:

Kindly amend claims 22, 24-26, 31 and 33 as follows:

Kindly replace claim 22 with the following amended claim 22:

22. (Amended) The method for fabricating a semiconductor device according to claim 21, wherein the gate spacers are formed by atomic layer deposition of a multi-layer of a silicon oxide layer and a silicon nitride layer.

The changes in the previous claim are indicated by brackets for deletions and underlining for insertions.

22. (Amended) The method for fabricating a semiconductor device according to claim 21, wherein the gate spacers are formed by atomic layer deposition of a multi-layer of a silicon oxide layer and a silicon nitride layer [by atomic layer deposition].

Kindly replace claim 24 with the following amended claim 24:

24. (Amended) The method for fabricating a semiconductor device according to claim 23, wherein the second bubble prevention layer is formed without a vacuum break.

The changes in the previous claim are indicated by brackets for deletions and underlining for insertions.

24. (Amended) The method for fabricating a semiconductor device according to claim [22] 23, wherein the second bubble prevention layer is formed without a vacuum break.

Kindly replace claim 25 with the following amended claim 25:

25. (Amended) The method for fabricating a semiconductor device according to claim 23, wherein the bit line spacers are formed by atomic layer deposition of a multi-layer of a silicon nitride layer and a silicon oxide layer.

The changes in the previous claim are indicated by brackets for deletions and underlining for insertions.

25. (Amended) The method for fabricating a semiconductor device according to claim [22] 23, wherein the bit line spacers are formed by atomic layer deposition of a multi-layer of a silicon nitride layer and a silicon oxide layer [by atomic layer deposition].

Kindly replace claim 26 with the following amended claim 26:

26. (Amended) The method for fabricating a semiconductor device according to claim 21, wherein each gate stack pattern is formed by sequentially stacking a gate insulating layer, a first gate conductive layer, a second gate conductive layer, and a gate capping layer.

The changes in the previous claim are indicated by brackets for deletions and underlining for insertions.

26. (Amended) The method for fabricating a semiconductor device according to claim [20] 21, wherein each gate stack pattern is formed by sequentially stacking a gate insulating layer, a first gate conductive layer, a second gate conductive layer, and a gate capping layer.

Kindly replace claim 31 with the following amended claim 31:

31. (Amended) The method for fabricating a semiconductor device according to claim 23, wherein each bit line stack pattern is formed by sequentially stacking a barrier metal layer, a bit line conductive layer, and a bit line capping layer.

The changes in the previous claim are indicated by brackets for deletions and underlining for insertions.

31. (Amended) The method for fabricating a semiconductor device according to claim [22] 23, wherein each bit line stack pattern is formed by sequentially stacking a barrier metal layer, a bit line conductive layer, and a bit line capping layer.

Kindly replace claim 33 with the following amended claim 33:

33. (Amended) The method for fabricating a semiconductor device according to claim 32, wherein the liner layer is formed by atomic layer deposition of a multi-layer of a silicon nitride layer and a silicon oxide layer [by atomic layer deposition], and the gate spacers and the bit line spacers are formed by atomic layer deposition of a multi-layer of a silicon oxide layer and a silicon nitride layer [by atomic layer deposition].

The changes in the previous claim are indicated by brackets for deletions and underlining for insertions.

33. (Amended) The method for fabricating a semiconductor device according to claim 32, wherein the liner layer is formed by atomic layer deposition of a multi-layer of a silicon nitride layer and a silicon oxide layer [by atomic layer deposition], and the gate spacers and the bit line spacers are formed by atomic layer deposition of a multi-layer of a silicon oxide layer and a silicon nitride layer [by atomic layer deposition].